Silicon Carbide Schottky Diode

General Description

This product family offers state of the art performance. It is designed for high frequency applications where high efficiency and high reliability are required.

Features

- Low conduction loss due to low VF
- Extremely low switching loss by tiny Qc
- Highly rugged due to better surge current
- Industrial standard quality and reliability

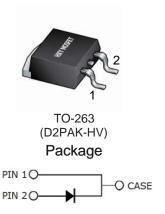
Applications

- UPS
- Power Inverter
- High performance SMPS
- Power factor correction

Ordering Part Number	Package	Qty(PCS)	
HSTPSC10H12G2YTR	TO-263(D2PAK-HV)	800	







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Maximum Ratings (at Tj = 25 °C, unless otherwise specified)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	Vrrm	1200	V
Surge Peak Reverse Voltage	Vrsm	1200	V
DC Peak Reverse Voltage	Vr	1200	V
Continuous Forward Current Tc = 25°C Tc = 135°C Tc = 160°C	lF	30 15 10	А
Repetitive Peak Forward Surge Current $Tc = 25^{\circ}C, t_p = 10 \text{ms,Half Sine Pulse}$ $Tc = 110^{\circ}C, t_p = 10 \text{ms,Half Sine Pulse}$	IFRM	57 41.5	А
Non-Repetitive Forward Surge Current $T_C = 25^{\circ}C, t_p=10 \text{ms}$, Half Sine Pulse $T_C = 110^{\circ}C, t_p=10 \text{ms}$, Half Sine Pulse	Ifsм	90 69.5	А
i^2 dt value $T_C = 25^{\circ}C, t_p = 10 ms, Half Sine Pulse T_C = 110^{\circ}C, t_p = 10 ms, Half Sine Pulse$	∫ i²dt	40.5 24	A²s
Power dissipation $Tc = 25^{\circ}C$ $Tc = 110^{\circ}C$	Ptot	115 50	W
Operating junction Range	Tj	-55 to +175	°C
Storage temperature Range	Tstg	-55 to +150	°C

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal resistance, junction - case.	RthJC	1.30	°C/W

Electrical Characteristic (at Tj = 25 °C, unless otherwise specified)

Parameter	Symbol	Value		Unit	Test Condition		
i arameter	Oymboi	min.	typ.	max.	Offic	rest condition	
Forward Voltage	VF				V	I _F =10A	
		-	1.4	1.7		T _j =25°C	
		-	2.0	-		Tj=175°C	
					μА	V _R =1200V	
Reverse Current	lR	-	-	100		T _j =25°C	
		-	-	200		T _j =175°C	
					nC	V _R =800V,T _j =25℃	
Total Capacitive Charge	Qc	-	48	-		$Q_C = \int_0^{V_R} C(V) dV$	
Total Capacitance	С				pF	Tj=25℃, f=1MHz	
		-	695	-		V _R =0V	
		-	46	-		V _R =400V	
		-	35	-		Vr=800V	

Characteristics Curve:

Fig 1: Forward Characteristics

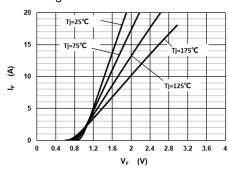


Fig 3: Current Derating

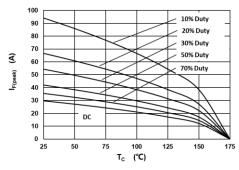


Fig 2: Reverse Characteristics

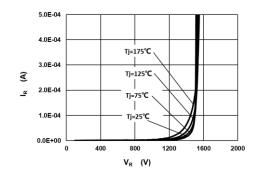
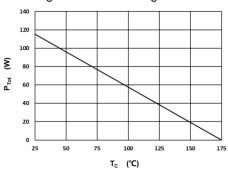


Fig 4: Power Derating



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Fig 5: Capacitance vs. Reverse Voltage

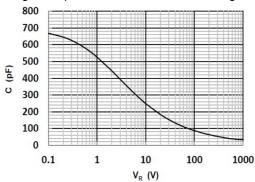


Fig 6: Reverse Charge vs. Reverse Voltage

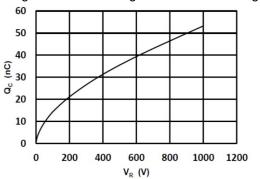


Fig 7: Typical Capacitance Stored Energy

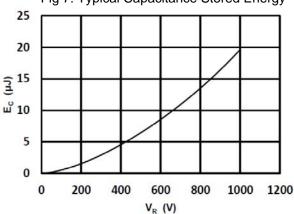
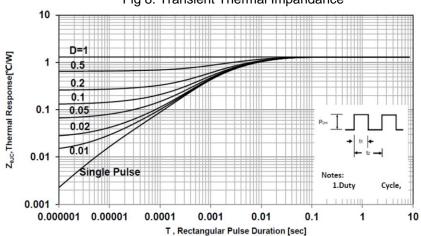


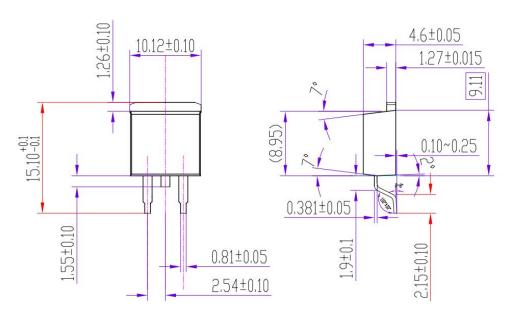
Fig 8: Transient Thermal Impandance

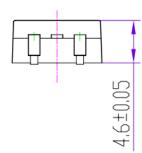


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Package Dimensions

Package TO-263(D2PAK-HV)





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